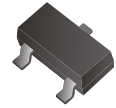


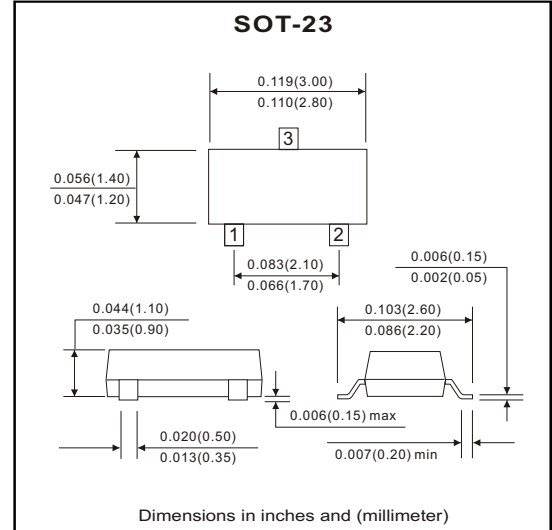
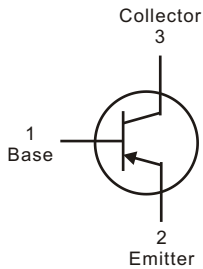
MMBT4403-G (PNP) RoHS Device



Features

-Switching transistor.

Marking: 2T



Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base voltage	V _{CBO}	-40	V
Collector-Emitter voltage	V _{CEO}	-40	V
Emitter-Base voltage	V _{EBO}	-5	V
Collector current-continuous	I _C	-0.6	A
Collector power dissipation	P _C	300	mW
Junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-55 to +150	°C

Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Collector-Base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-Emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-40			V
Emitter-Base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-35V, I _E =0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-35V, I _B =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-150mA	100		300	
Collector-Emitter saturation voltage	V _{CE(SAT)}	I _C =-150mA, I _B =-15mA			-0.4	V
Base-Emitter saturation voltage	V _{BE(SAT)}	I _C =-150mA, I _B =-15mA			-0.95	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-20mA f=100MHz	200			MHz

RATING AND CHARACTERISTIC CURVES (MMBT4403-G)

Fig. 1 Max. Power Dissipation vs. Ambient Temperature

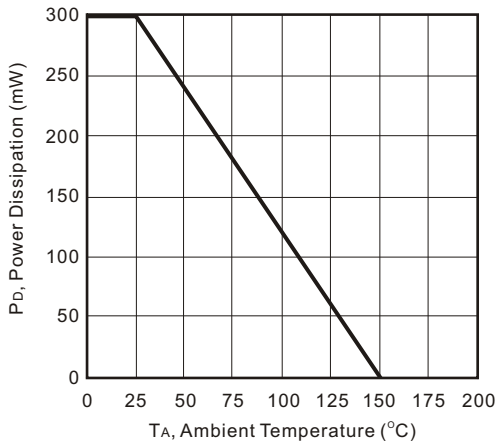


Fig. 2 Typical DC Current Gain vs. Collector Current

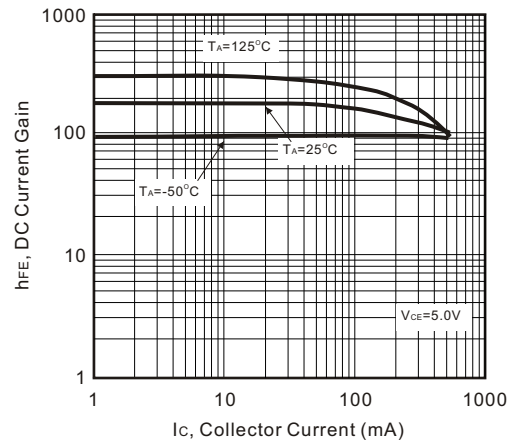


Fig. 3 Typical Capacitance

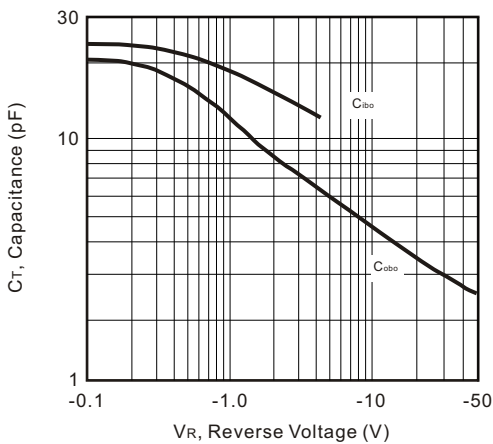


Fig. 4 Typical Collector Saturation Region

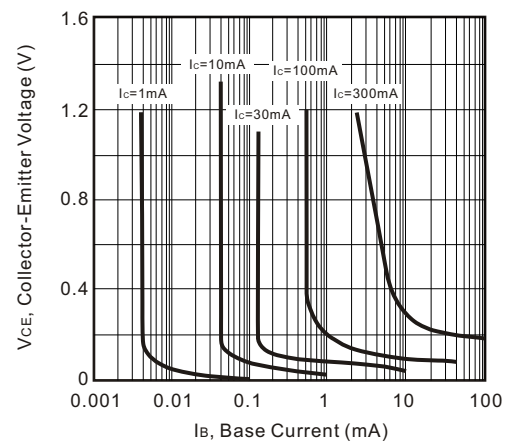


Fig. 5 Collector-Emmitter Saturation Voltage vs. Collector Current

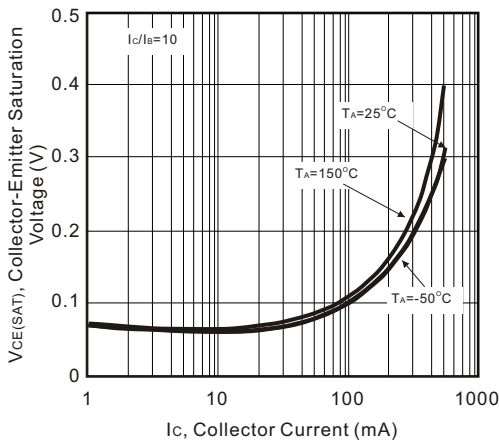


Fig. 6 Base-Emmitter Voltage vs. Collector Current

